

CEDM8001VL

**SURFACE MOUNT SILICON
P-CHANNEL
ENHANCEMENT-MODE
MOSFET**



Top View Bottom View

SOT-883VL CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CEDM8001VL is a P-Channel Enhancement-mode MOSFET packaged in the very low profile SOT-883VL case. The device is designed for space constrained high speed amplifier and driver applications where package height is a critical design element. This MOSFET offers low $r_{DS(ON)}$ and low gate charge.

MARKING CODE: 8

COMPLEMENTARY N-CHANNEL: CEDM7001VL

FEATURES:

- 100mW Power Dissipation
- 0.32mm very low package profile
- Low $r_{DS(ON)}$
- Low threshold voltage
- Logic level compatible
- Small leadless surface mount package

APPLICATIONS:

- Load/Power switches
- DC-DC converters
- Battery powered portable equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	10	V
Continuous Drain Current (Steady State)	I_D	100	mA
Continuous Drain Current	I_D	200	mA
Power Dissipation	P_D	100	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

SYMBOL

V_{DS}	20	V
V_{GS}	10	V
I_D	100	mA
I_D	200	mA
P_D	100	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

UNITS

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

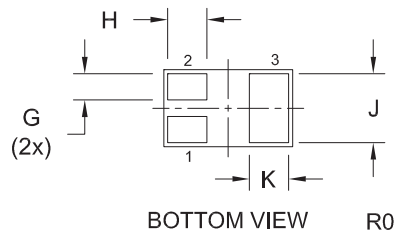
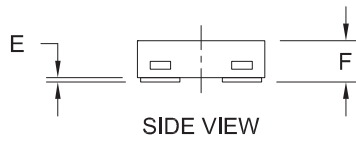
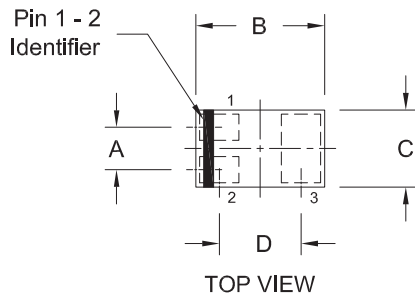
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=10\text{V}, V_{DS}=0$			1.0	μA
I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0$			1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=100\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.6		1.1	V
$r_{DS(ON)}$	$V_{GS}=4.0\text{V}, I_D=10\text{mA}$		1.9	8.0	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=10\text{mA}$		2.4	12	Ω
$r_{DS(ON)}$	$V_{GS}=1.5\text{V}, I_D=1.0\text{mA}$			45	Ω
g_{FS}	$V_{DS}=10\text{V}, I_D=100\text{mA}$	100			mS
C_{rss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		15		pF
C_{iss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		45		pF
C_{oss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		15		pF
$Q_{g(tot)}$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.658		nC
Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.158		nC
Q_{gd}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.181		nC
t_{on}	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$		35		ns
t_{off}	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$		80		ns

R2 (11-September 2014)

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SOT-883VL CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.014		0.35	
B	0.037	0.041	0.95	1.05
C	0.022	0.026	0.55	0.65
D	0.026		0.65	
E	0.000	0.002	0.00	0.05
F	0.012	0.013	0.30	0.32
G	0.004	0.008	0.10	0.20
H	0.008	0.012	0.20	0.30
J	0.018	0.022	0.45	0.55
K	0.008	0.012	0.20	0.30

SOT-883VL (REV:R0)

LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODE: 8

Package Type Options (all dimensions are maximum - in mm)

Package	Length	Width	Height	P _D (mW)	Central Item Number
SOT-883VL	1.05	0.65	0.32	100	CEDM8001VL
SOT-883L	1.05	0.65	0.40	100	CEDM8001
SOT-953	1.05	1.05	0.50	250	CMNDM8001
SOT-523	1.70	1.70	0.78	250	CMUDM8001

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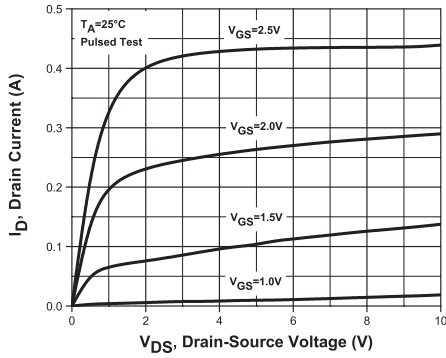
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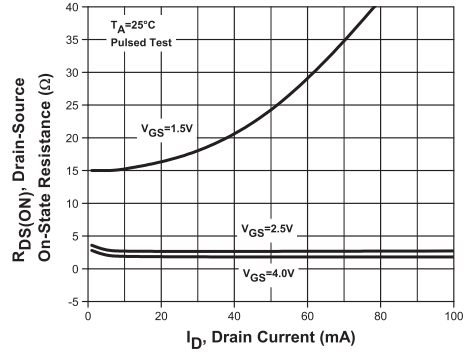


TYPICAL ELECTRICAL CHARACTERISTICS

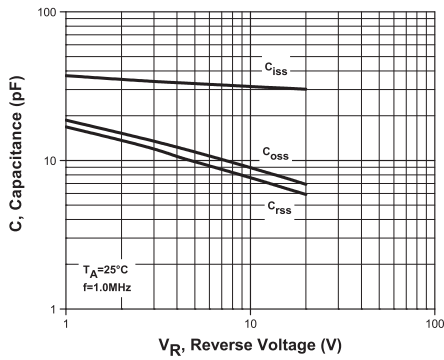
Output Characteristics



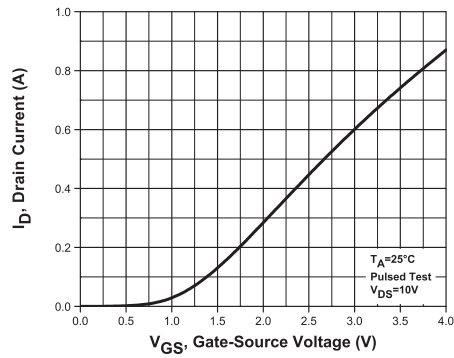
Drain Source On Resistance



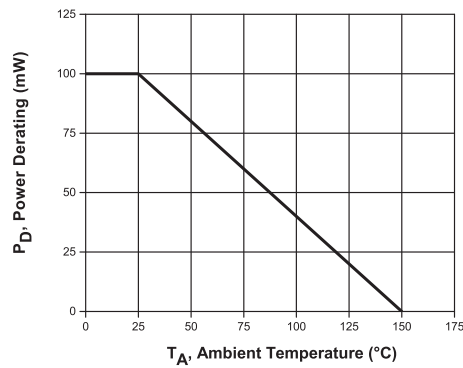
Capacitance



Transfer Characteristics



Power Derating



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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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